Comparative analysis of the hydrogen-vacancy interaction in Mg and Al based on density functional theory LARS ISMER, ANDERSON JAN-OTTI, Materials Department, University of California, Santa Barbara, CA 93106-5050, MIN SIK PARK, Department of Physics, Missouri University of Science and Technology, Rolla, MO 65409, CHRIS G. VAN DE WALLE, Materials Department, University of California, Santa Barbara, CA 93106-5050 — The interactions of vacancies (V) with atomic hydrogen (H) in the bulk of the metal are expected to play an important role in H-storage as well as H-embrittlement. Using density functional theory we have studied the H-V interactions in hcp-Mg and fcc-Al, two prototypic systems for H storage. We show that a single V can in principle host up to 9 H atoms in Mg and 10 in Al. In going beyond previous theoretical studies we further evaluate the concentration of the H-V complexes for different H loading conditions – ranging from low pressures to high pressures of H2 gas. We find significant differences between Mg and Al. In the case of Al, up to 15 % of H atoms are trapped in single vacancies even for very low H pressures, which strongly slows down the diffusion of H atoms. In the case of Mg, these trapping effects are negligible for low H pressures. However, vacancies containing multiple H atoms and H-induced superabundant vacancy formation are predicted to occur in Mg at much lower H loading pressures (about 1 GPa) than in Al (about 10 GPa).